



# PJM05P60SC

## P-Channel Enhancement Mode Power MOSFET

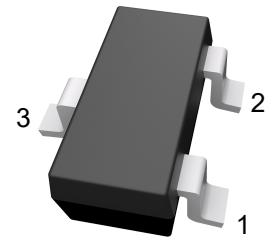
### Features

- Surface mount package
- High density cell design for ultra low  $R_{DS(on)}$
- $V_{DS} = -60V, I_D = -5A$   
 $R_{DS(on)} < 75m\Omega @ V_{GS} = -10V$

### Application

- Load switch and in PWM applications
- Power management

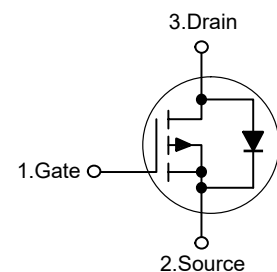
### SOT-23-3



1. Gate 2. Source 3. Drain

**Marking Code: KM**

### Schematic Diagram



### Absolute Maximum Ratings

Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$-V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$-I_D$	5	A
Drain Current-Pulsed <sup>Note1</sup>	$-I_{DM}$	16	A
Maximum Power Dissipation	$P_D$	1.5	W
Junction Temperature	$T_J$	150	°C
Storage Temperature Range	$T_{STG}$	-55 to +150	°C

### Thermal Characteristics

Maximum Junction-to-Case <sup>Note2</sup>	$R_{\theta JC}$	83.3	°C/W
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### Electrical Characteristics

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
Drain-Source Breakdown Voltage	$-V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu A$	60	--	--	V
Zero Gate Voltage Drain Current	$-I_{DSS}$	$V_{DS}=-60V, V_{GS}=0V$	--	--	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	--	--	$\pm 100$	nA
Gate Threshold Voltage <sup>Note3</sup>	$-V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	1	1.5	2	V
Drain-Source On-Resistance <sup>Note3</sup>	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-4A$	--	55	70	m $\Omega$
		$V_{GS}=-4.5V, I_D=-3A$	--	65	80	m $\Omega$
Forward Transconductance <sup>Note3</sup>	$g_{FS}$	$V_{DS}=-5V, I_D=-1A$	--	6	--	S
<b>Dynamic Characteristics</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=-30V, V_{GS}=0V, f=1MHz$	--	930	--	pF
Output Capacitance	$C_{oss}$		--	85	--	pF
Reverse Transfer Capacitance	$C_{rss}$		--	35	--	pF
<b>Switching Characteristics</b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-30V, V_{GS}=-10V, R_{GEN}=3\Omega, R_L=7.5\Omega$	--	8	--	nS
Turn-on Rise Time	$t_r$		--	4	--	nS
Turn-off Delay Time	$t_{d(off)}$		--	32	--	nS
Turn-off Fall Time	$t_f$		--	7	--	nS
Total Gate Charge	$Q_g$	$V_{DS}=-30V, I_D=-10A, V_{GS}=-4V$	--	25	--	nC
Gate-Source Charge	$Q_{gs}$		--	3	--	nC
Gate-Drain Charge	$Q_{gd}$		--	7	--	nC
<b>Source-Drain Diode Characteristics</b>						
Diode Forward Voltage <sup>Note3</sup>	$-V_{SD}$	$V_{GS}=0V, I_S=-5A$	--	--	1.2	V
Diode Forward Current <sup>Note2</sup>	$-I_S$		--	--	5	A

Note: 1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.

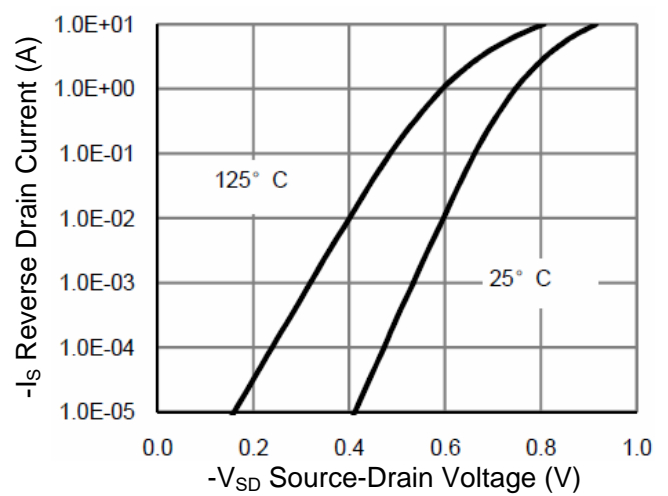
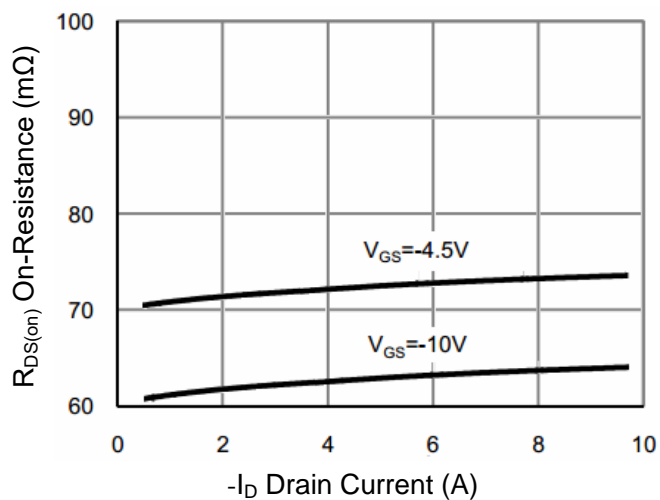
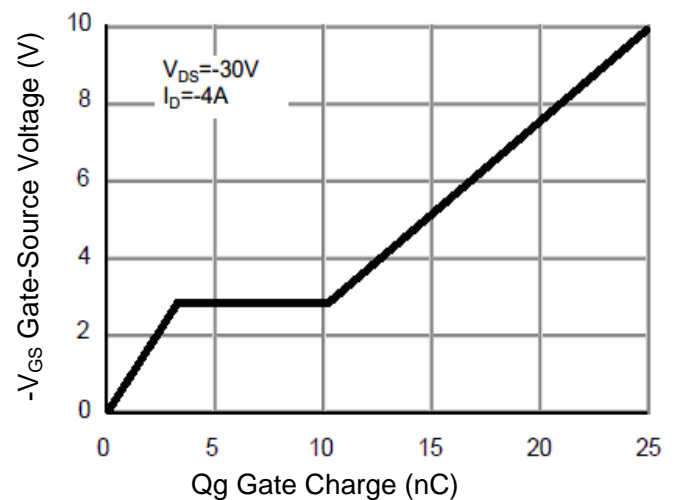
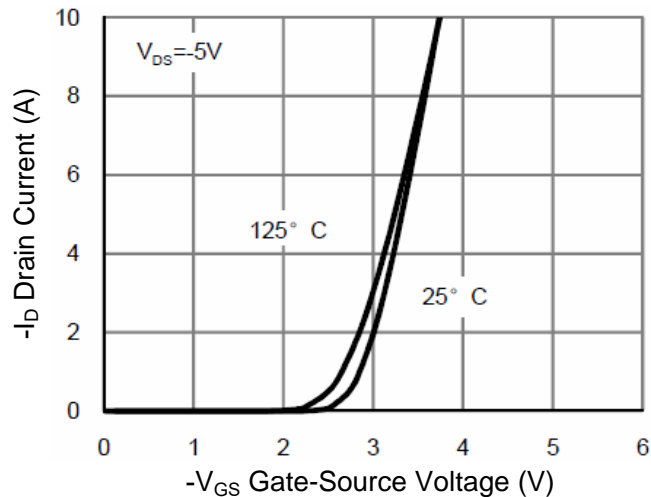
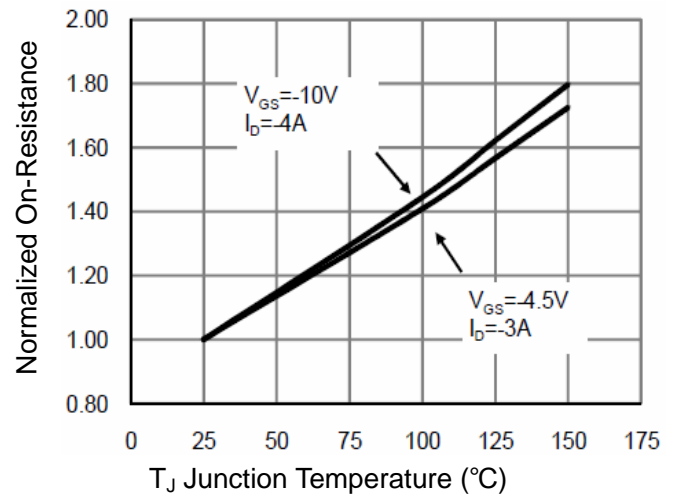
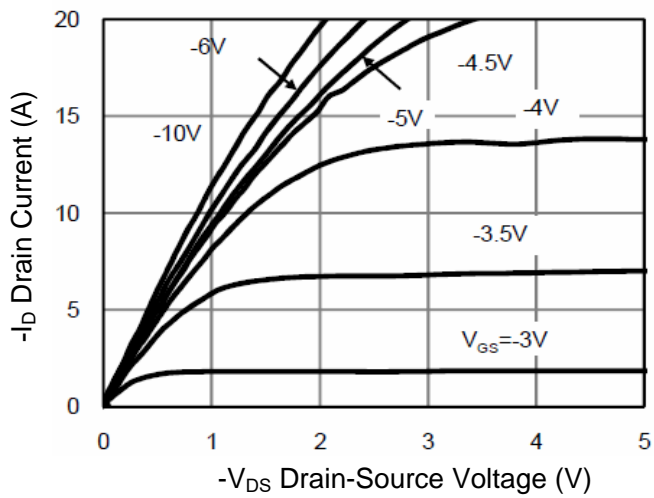
3. Pulse Test: Pulse width  $\leq 300\mu s$ , duty cycles  $\leq 2\%$ .



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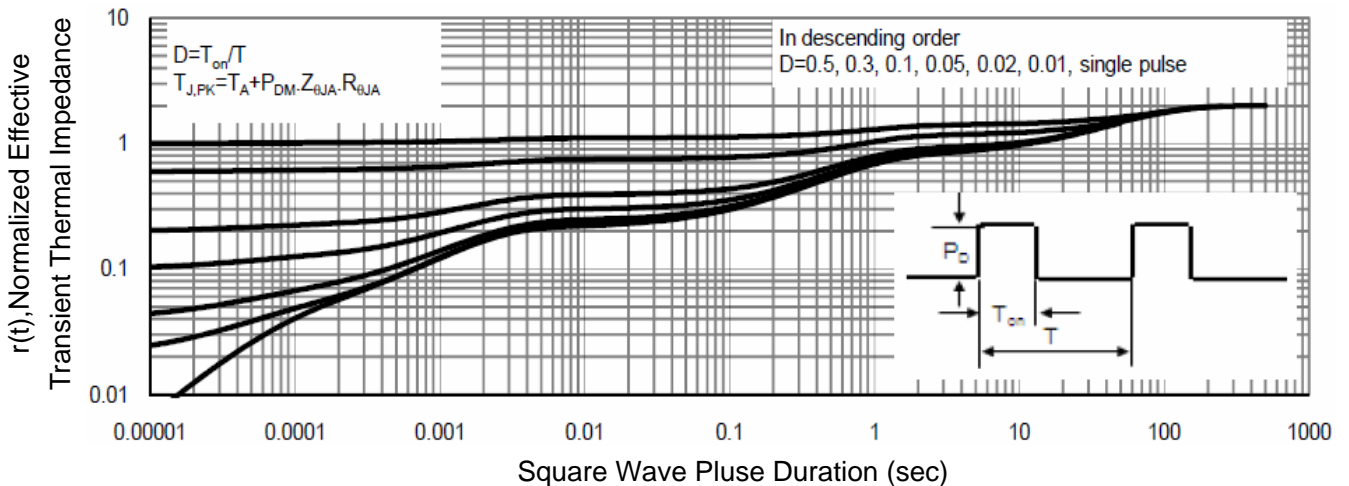
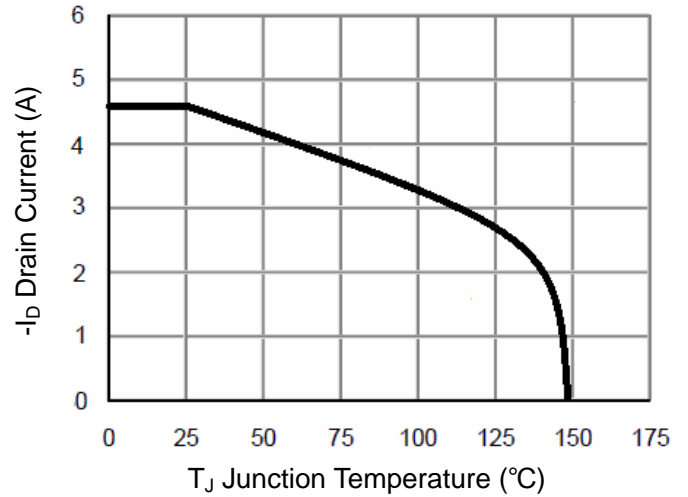
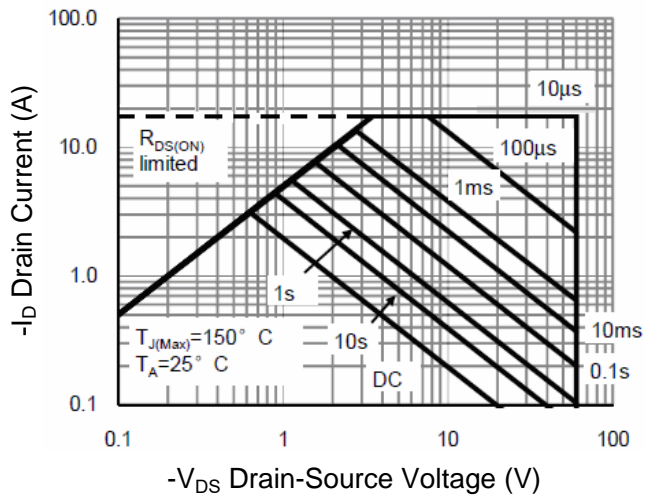
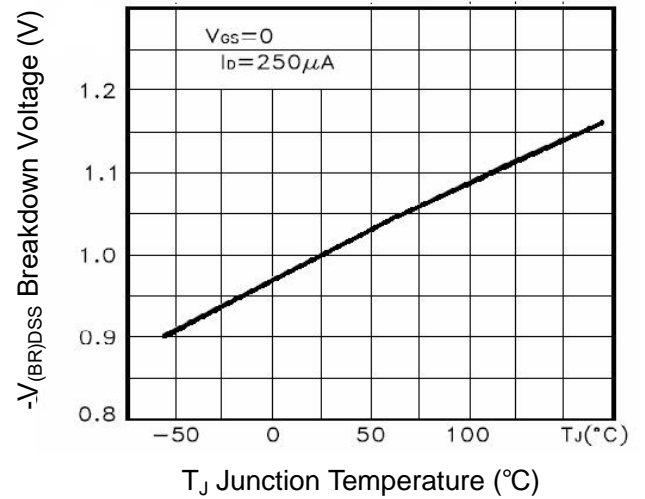
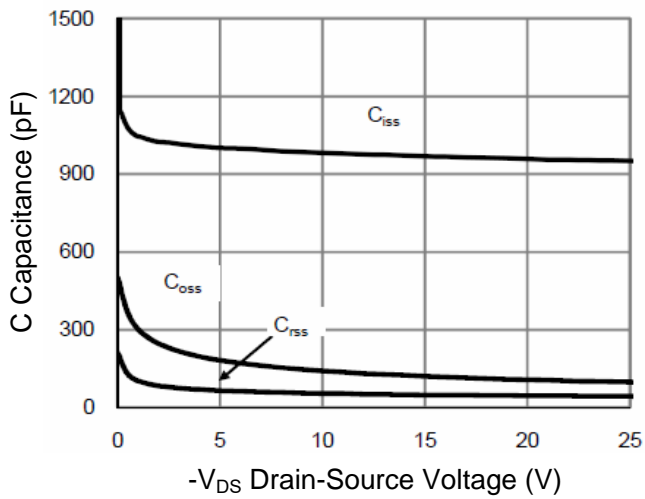
### Typical Characteristic Curves

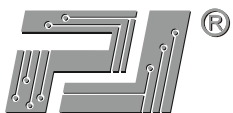




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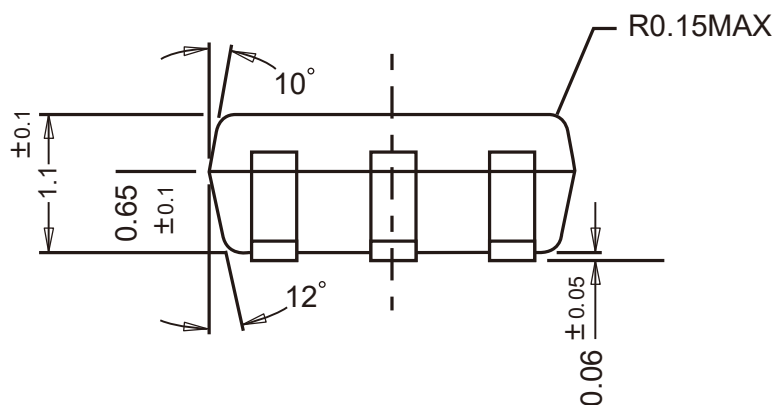
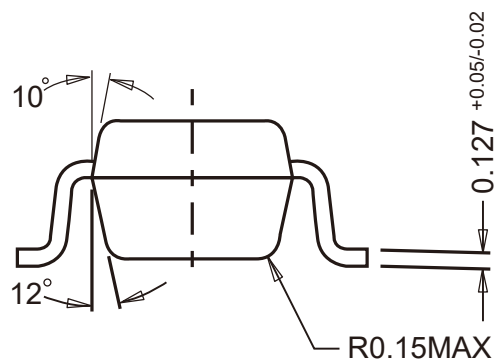
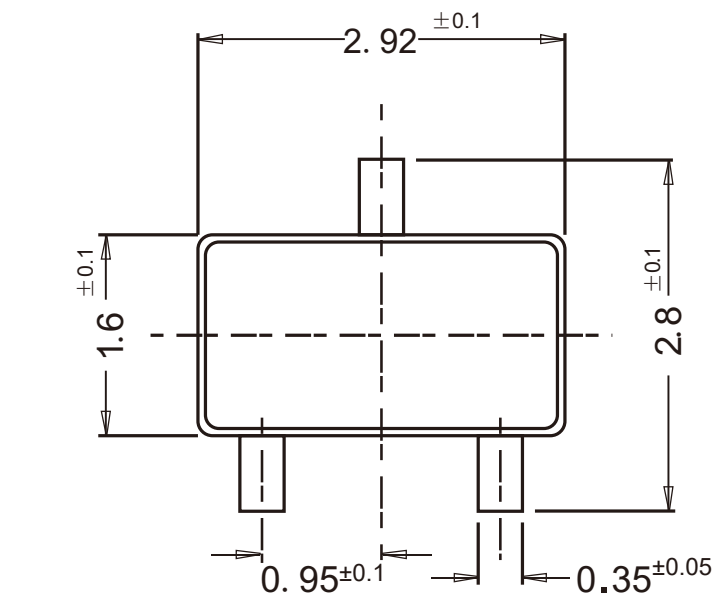
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## P-Channel Enhancement Mode Power MOSFET

### Package Outline

SOT-23-3

Dimensions in mm



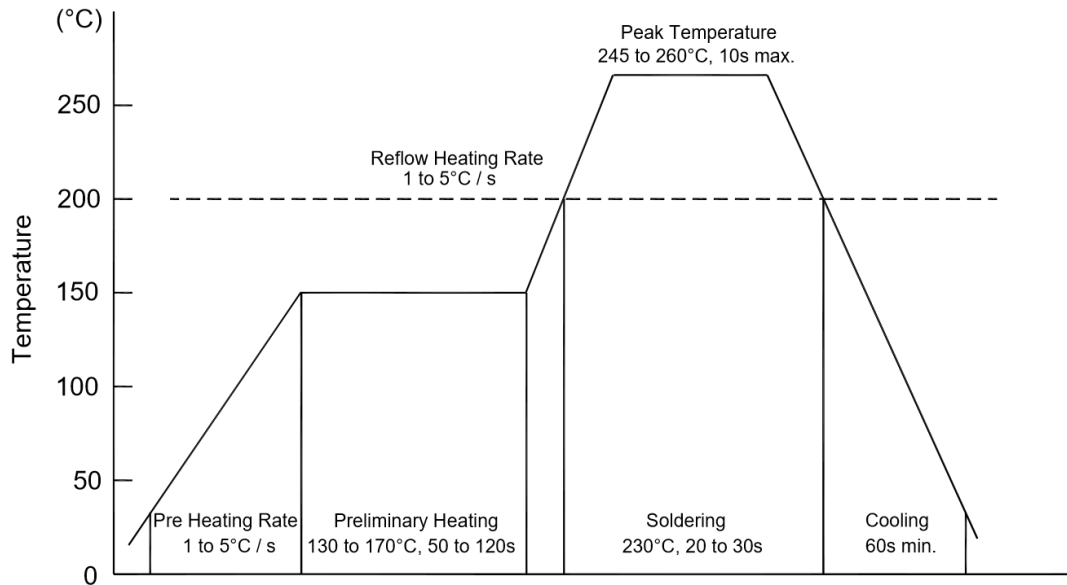
### Ordering Information

Device	Package	Shipping
PJM05P60SC	SOT-23-3	3,000PCS/Reel&7inches



### Conditions of Soldering and Storage

#### ◆ Recommended condition of reflow soldering



Recommended peak temperature is over 245 °C. If peak temperature is below 245 °C, you may adjust the following parameters:

- Time length of peak temperature (longer)
- Time length of soldering (longer)
- Thickness of solder paste (thicker)

#### ◆ Conditions of hand soldering

- Temperature: 370 °C
- Time: 3s max.
- Times: one time

#### ◆ Storage conditions

- **Temperature**  
5 to 40 °C
- **Humidity**  
30 to 80% RH
- **Recommended period**  
One year after manufacturing

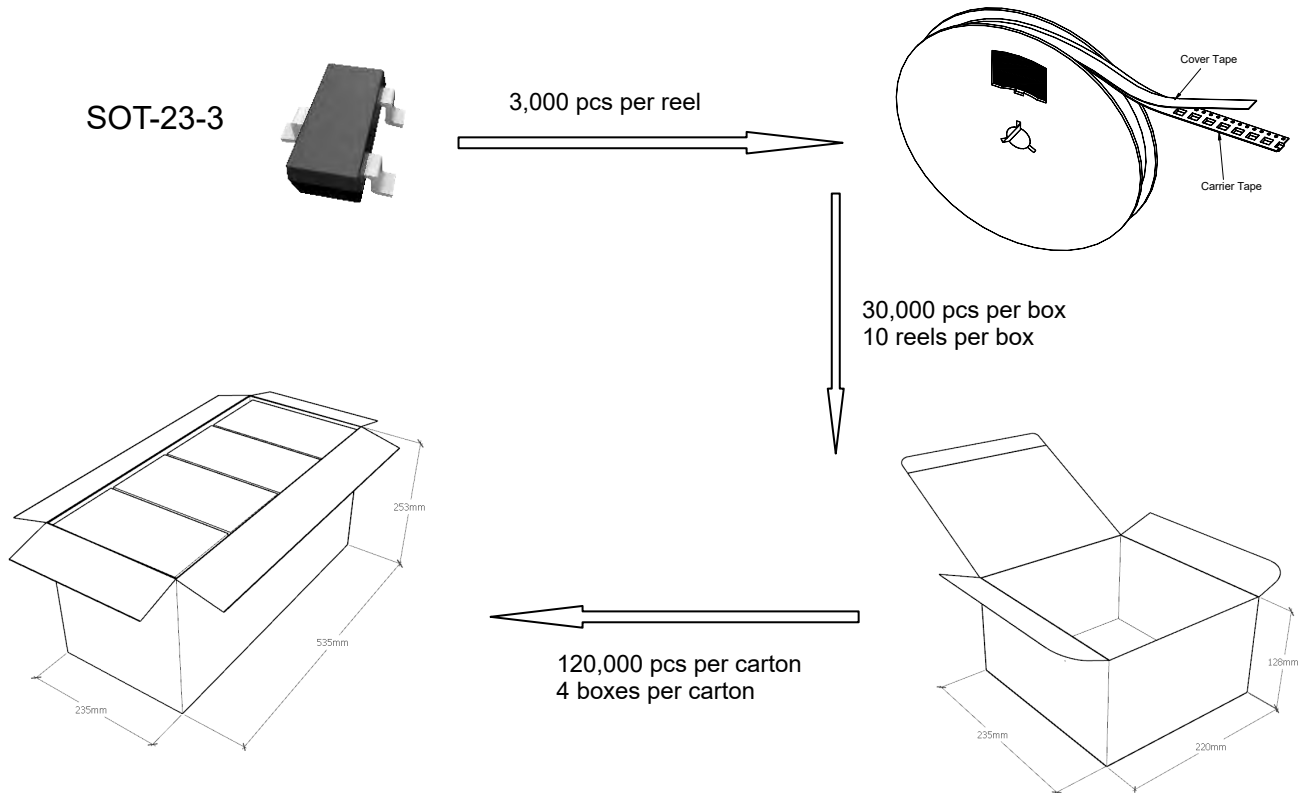


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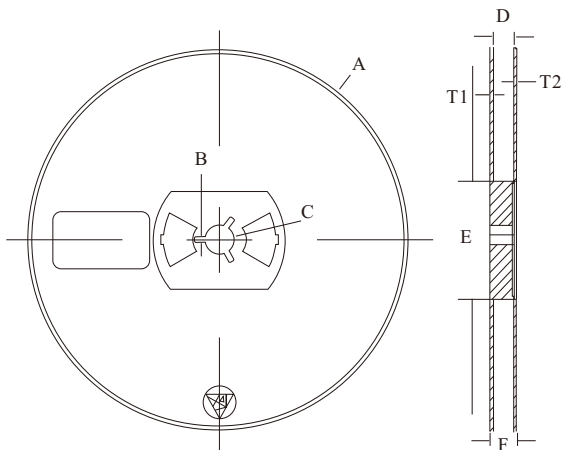
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### Package Specifications

- The method of packaging

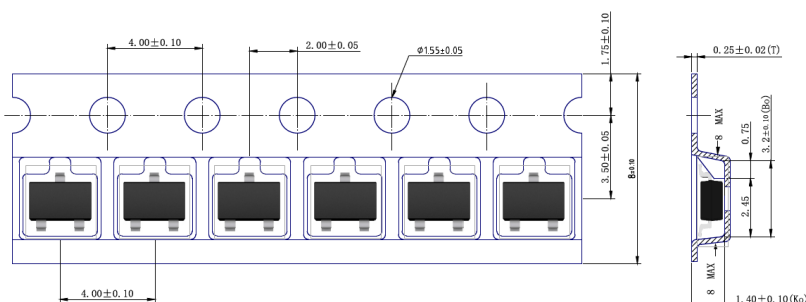


### ◆ Embossed tape and reel data



Symbol	Value (unit: mm)
A	Ø 177.8±1
B	2.7±0.2
C	Ø 13.5±0.2
E	Ø 54.5±0.2
F	12.3±0.3
D	9.6+2/-0.3
T1	1.0±0.2
T2	1.2±0.2

Reel (7")



单击下面可查看定价，库存，交付和生命周期等信息

[>>PJSEMI\(平晶微\)](#)